

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ max	$I_D$ max $T_A = +25^\circ C$
30V	16m $\Omega$ @ $V_{GS} = 10V$	9.8A
	23m $\Omega$ @ $V_{GS} = 4.5V$	8.7A

## Description

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

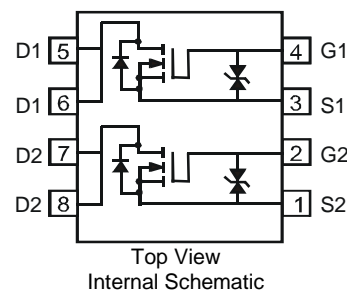
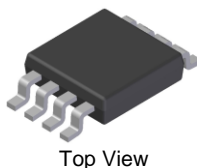
- Backlighting
- Power Management Functions
- DC-DC Converters

## Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

## Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.072 grams (Approximate)

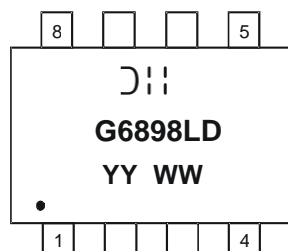


## Ordering Information (Notes 4 & 5)

Part Number	Qualification	Case	Packaging
DMG6898LSD-13	Commercial	SO-8	2,500 / Tape & Reel
DMG6898LSDQ-13	Automotive	SO-8	2,500 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to [http://www.diodes.com/quality/product\\_compliance\\_definitions/](http://www.diodes.com/quality/product_compliance_definitions/).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



DII = Manufacturer's Marking  
 G6898LD = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY or YY = Year (ex: 14 = 2014)  
 WW = Week (01 - 53)

**Maximum Ratings** @T<sub>A</sub> = +25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Continuous Drain Current (Note 6)	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	9.5	A
		T <sub>A</sub> = +85°C		7.1	
Pulsed Drain Current (Note 7)			I <sub>DM</sub>	30	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P <sub>D</sub>	1.28	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 6)	R <sub>θJA</sub>	99.3	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** @T<sub>A</sub> = +25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	-	-	1.0	μA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±10	μA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	1.0	1.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	-	11	16	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 9.4A
			17	23		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 8.3A
Forward Transfer Admittance	Y <sub>fs</sub>	-	17	-	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 9.4A
Diode Forward Voltage	V <sub>SD</sub>	-	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.3A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	-	1149	-	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	-	157	-	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	142	-	pF	
Gate Resistance	R <sub>g</sub>	-	1.51	-	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	-	11.6	-	nC	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 9.4A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	-	26	-	nC	
Gate-Source Charge	Q <sub>gs</sub>	-	2.7	-	nC	
Gate-Drain Charge	Q <sub>gd</sub>	-	3.4	-	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	-	11.67	-	ns	V <sub>DD</sub> = 10V, V <sub>GS</sub> = 4.5V, R <sub>GEN</sub> = 6Ω, I <sub>D</sub> = 1A
Turn-On Rise Time	t <sub>r</sub>	-	12.49	-	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	35.89	-	ns	
Turn-Off Fall Time	t <sub>f</sub>	-	12.33	-	ns	

- Notes:
6. Device mounted on FR-4 PCB, with minimum recommended pad layout.
  7. Repetitive rating, pulse width limited by junction temperature.
  8. Short duration pulse test used to minimize self-heating effect.
  9. Guaranteed by design. Not subject to production testing.

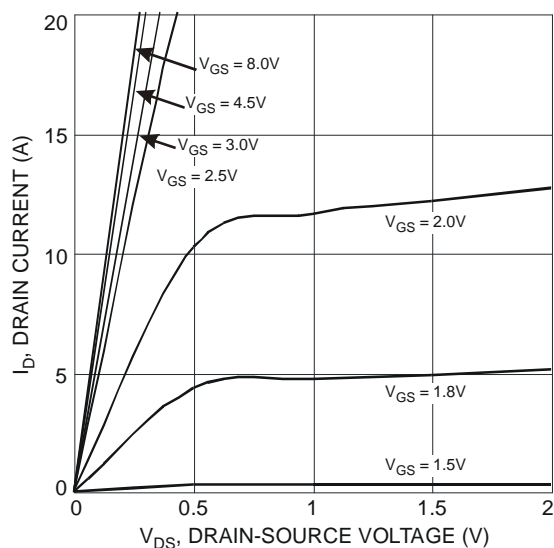


Fig. 1 Typical Output Characteristic

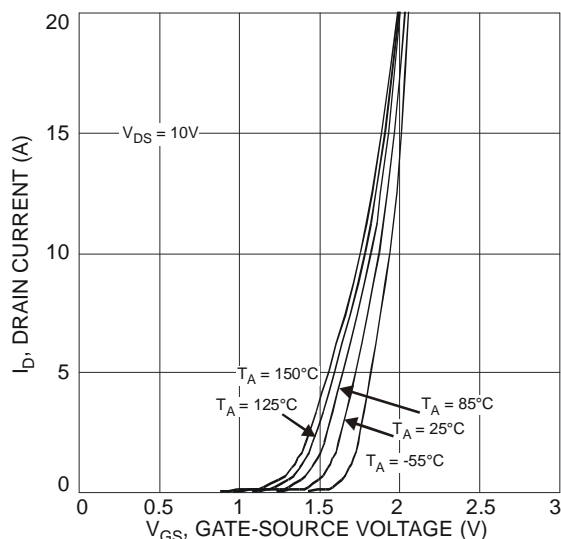


Fig. 2 Typical Transfer Characteristic

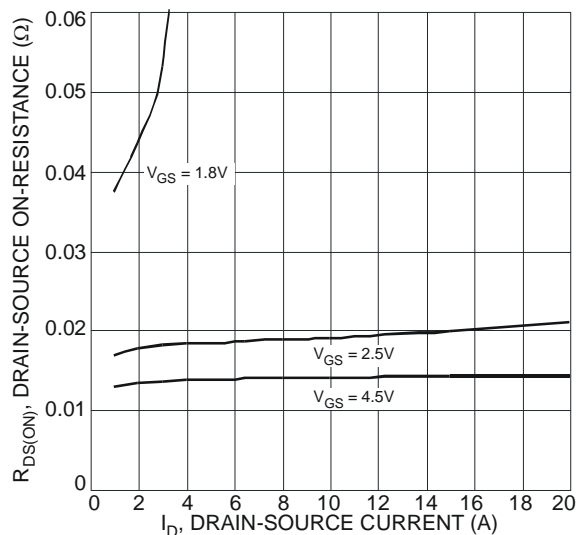


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

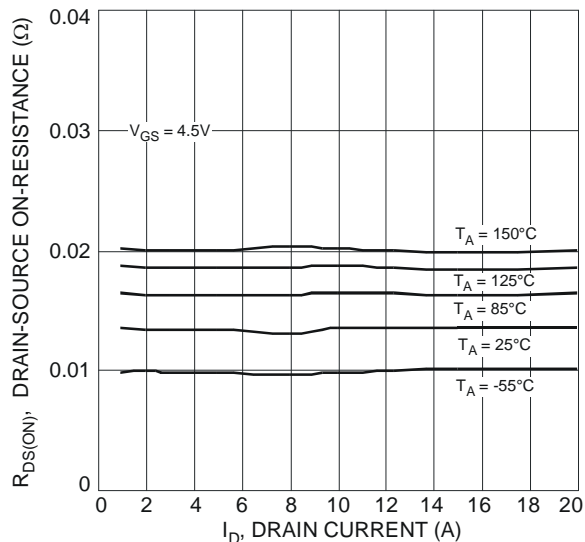


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

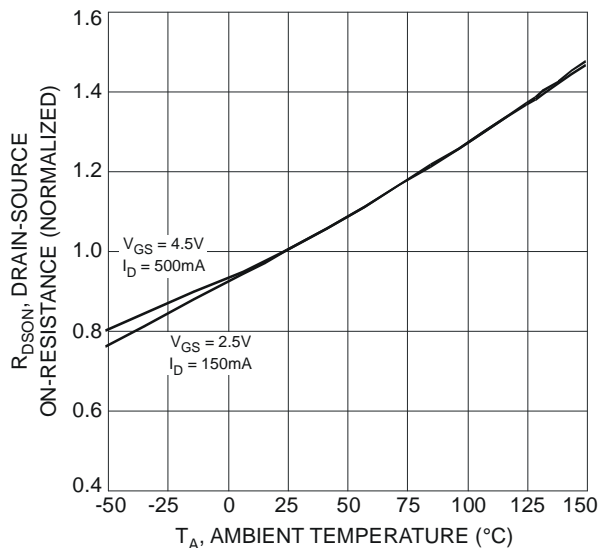


Fig. 5 On-Resistance Variation with Temperature

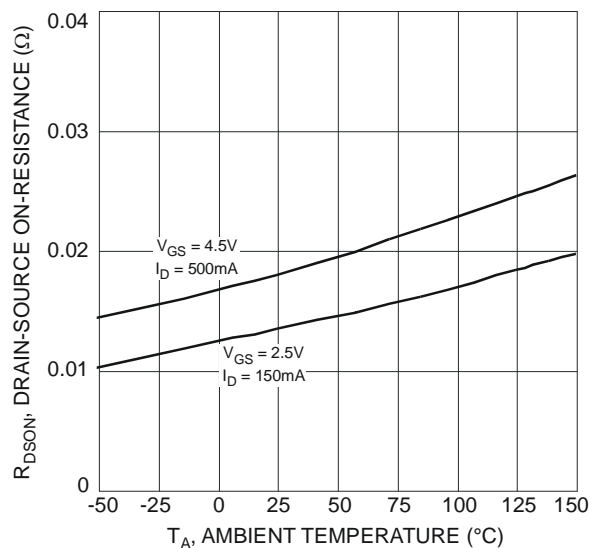


Fig. 6 On-Resistance Variation with Temperature

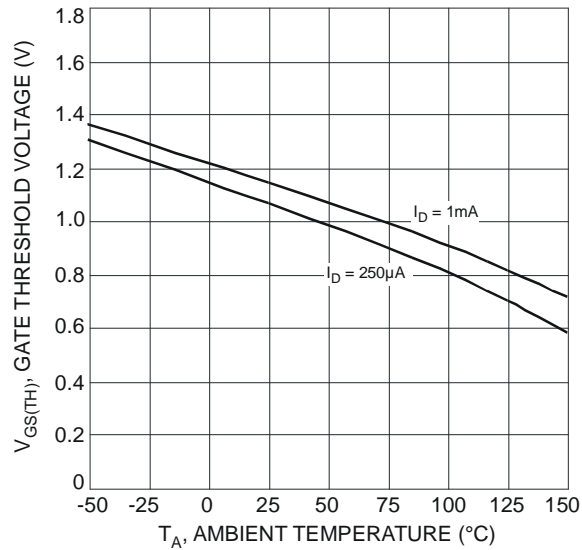


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

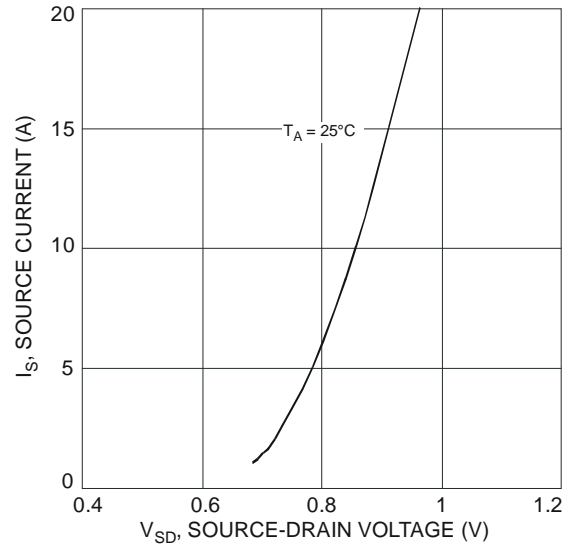


Fig. 8 Diode Forward Voltage vs. Current

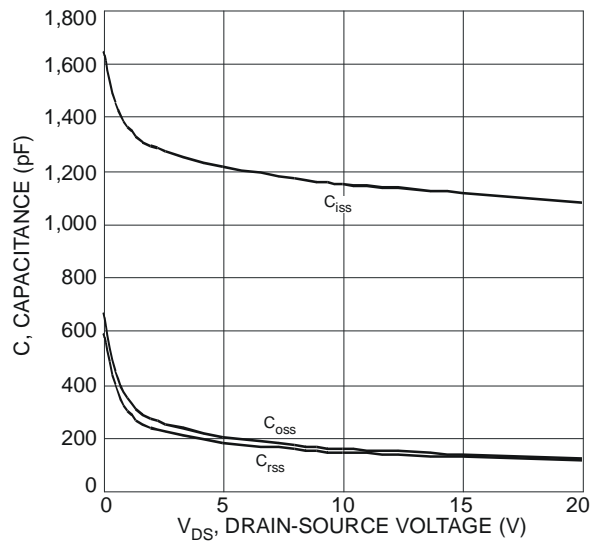


Fig. 9 Typical Total Capacitance

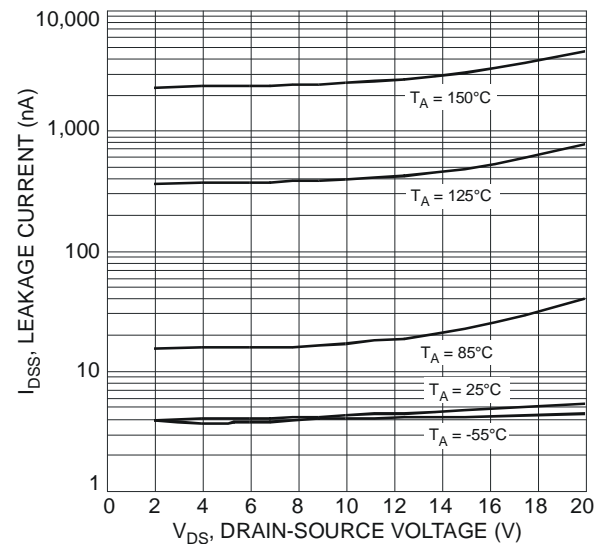


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

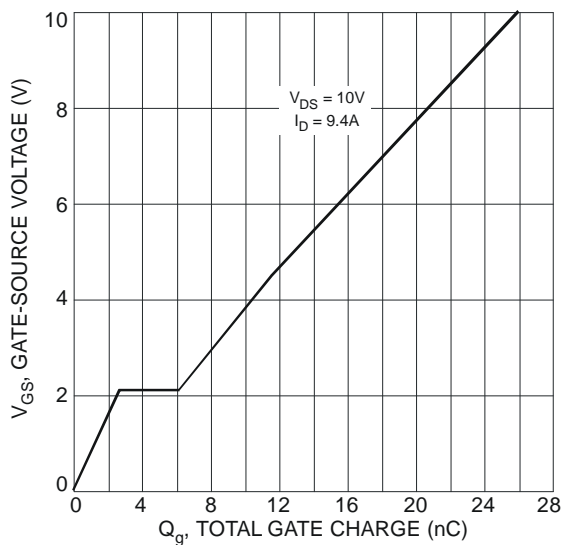


Fig. 11 Gate-Source Voltage vs. Total Gate Charge

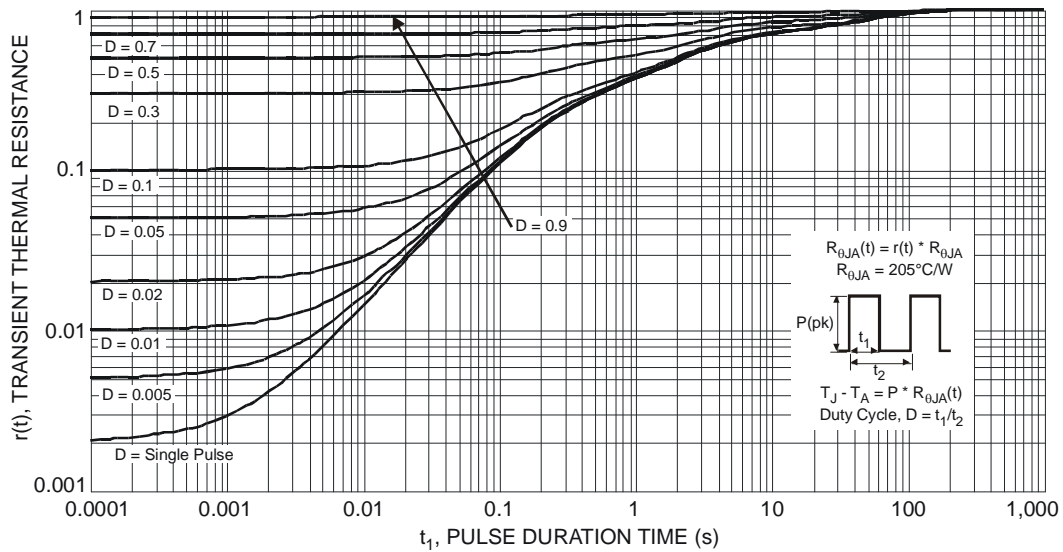
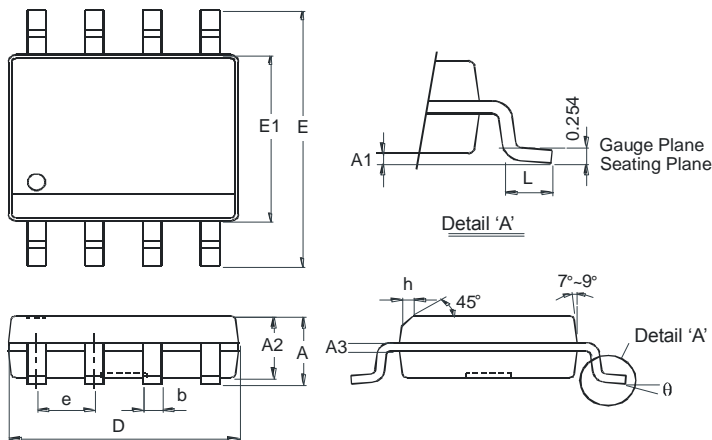


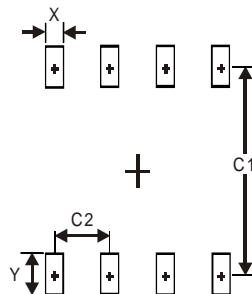
Fig. 12 Transient Thermal Response

## Package Outline Dimensions

 Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.


SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

## Suggested Pad Layout

 Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.


Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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